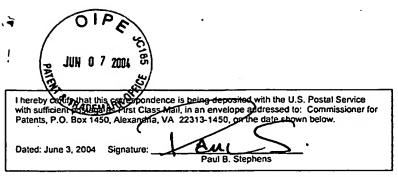
Silsie



Docket No.: 30205/37980A

(PATENT)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Seon Y. Cha

Application No.: 10/663,892

Art Unit: 2812

Filed: September 16, 2003

Examiner: J. Jey Tsai

For: Magnetic Random Access Memory Having

Transistor of Vertical Structure with Writing Line

Formed on an Upper Portion of the Magnetic

**Tunnel Junction Cell** 

## **AMENDMENT UNDER 37 CFR §1.312**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

## **INTRODUCTORY COMMENTS**

Please amend the above-identified U.S. patent application as follows:

Amendments to the Specification begin on page 2 of this paper.

Remarks begin on page 3 of this paper.

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